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(71) Applicant: **ADVANCED MICRO DEVICES, INC.** [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors: **YANG, Kai**; 1596 Bellemeade St, San Jose, CA 95131 (US). **ERB, Darrell, M.**; 1100 Runnymead Drive, Los Altos, CA 94024 (US). **WANG, Fei**; 6005 Wellfleet Way, San Jose, CA 95129 (US).

(74) Agent: **RODDY, Richard, J.**; Advanced Micro Devices, Inc., One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

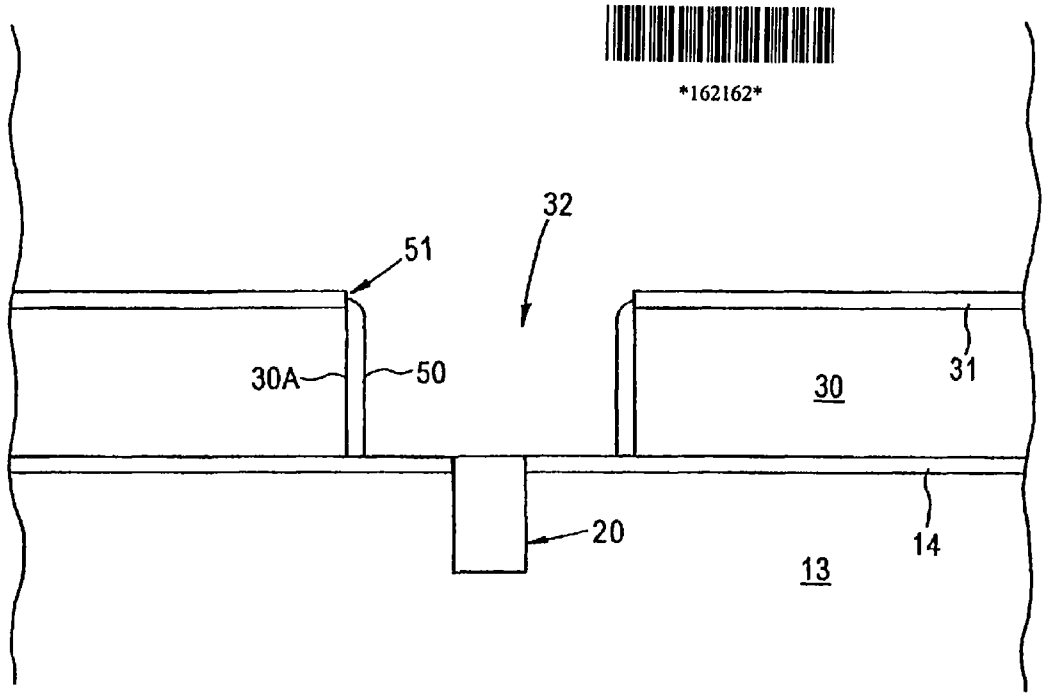
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(54) Title: DAMASCENE PROCESSING USING DIELECTRIC BARRIER FILMS



(57) Abstract: Damascene processing is implemented with dielectric barrier films (50, 90, 91) for improved step coverage and reduced contact resistance. Embodiments include the use of two different dielectric films (50, 31) to avoid misalignment problems. Embodiments further include dual damascene (100A, 100B) processing using Cu metallization (100).

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